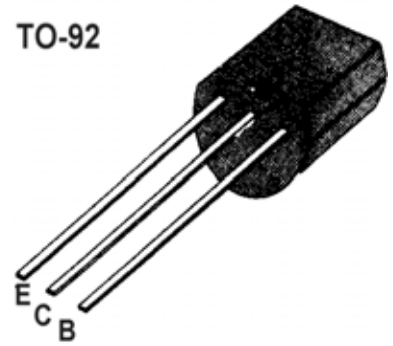


■■ APPLICATION: General Purpose Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-500	mA
Collector Power Dissipation	P _c	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE1}	85		340		V _{CE} = -10V, I _c = -150mA
	h _{FE2}	40				V _{CE} = -10V, I _c = -500mA
Collector Cut-off Current	I _{CB0}			-0.1	μA	V _{CB} = -20V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -3V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	-60			V	I _c = -0.01mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50			V	I _c = -10mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.01mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.35	-0.6	V	I _c = -300mA, I _B = -30mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		-1.1	-1.5	V	I _c = -300mA, I _B = -30mA
Gain bandwidth product	f _T	100	200		MHz	I _c = -50mA, V _{CE} = -10V, f = 200 MHz
Common Base Output Capacitance	C _{ob}		6	15	pF	V _{CB} = -10V, I _E =0, f = 1 MHz

■■ h_{FE} Classification

Classification	Q	R	S
h _{FE}	85~170	120~240	170~340